



SOT-23 Plastic-Encapsulate Transistors

MMBTA55LT1 TRANSISTOR (PNP) MMBTA56LT1

FEATURES

Power dissipation

P_{CM} : 0.225 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

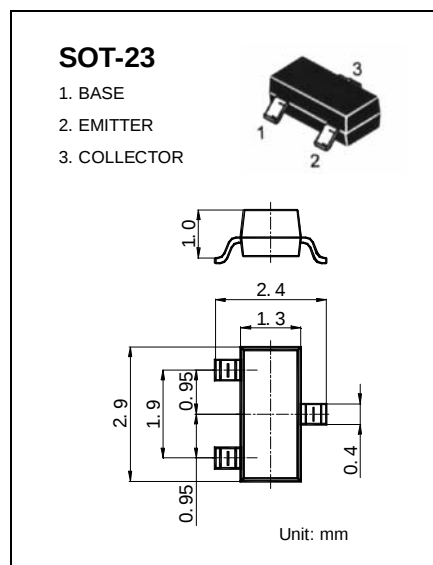
Collector-base voltage

V_{CBO} : MMBTA55: -60 V

MMBTA56: -80 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	MMBTA55 MMBTA56 V_{CBO}	$I_C=-100\mu A, I_E=0$	-60 -80		V
Collector-emitter breakdown voltage	MMBTA55 MMBTA56 V_{CEO}	$I_C=-1\text{ mA}, I_B=0$	-60 -80		V
Emitter-base breakdown voltage	MMBTA55 MMBTA56 V_{EBO}	$I_E=-100\mu A, I_C=0$	-4		V
Collector cut-off current	MMBTA55 MMBTA56 I_{CBO}	$V_{CB}=-60V, I_E=0$ $V_{CB}=-80V, I_E=0$		-0.1 -0.1	μA
Collector cut-off current	MMBTA55 MMBTA56 I_{CEO}	$V_{CE}=-50V, I_B=0$ $V_{CE}=-60V, I_B=0$		-0.1 -0.1	μA
DC current gain	MMBTA55 MMBTA56 $h_{FE(1)}$	$V_{CE}=-1V, I_C=-10\text{mA}$	100		
		$V_{CE}=-1V, I_C=-100\text{mA}$	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{ mA}$		-0.25	V
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE}=-1V, I_C=-100\text{ mA},$		-1.2	V
Transition frequency	f_T	$V_{CE}=-1V, I_C=-100\text{mA}$ $f=100\text{MHz}$	50		MHz

Marking	MMBTA55LT1: 2H;MMBTA56LT1: 2GM
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